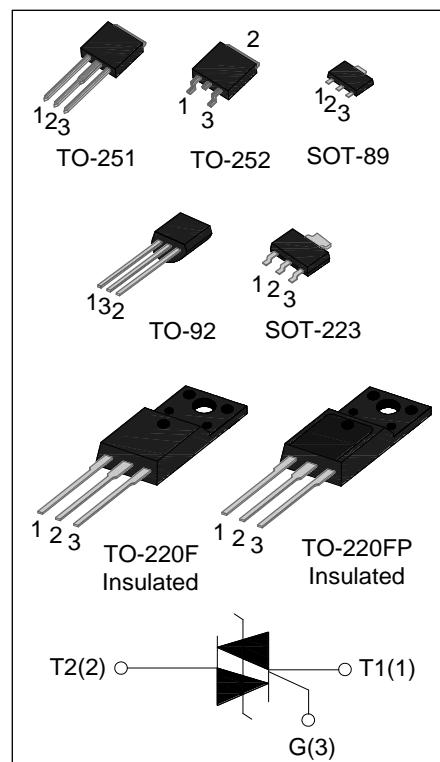


ACJT2 Series 2A TRIACs

Rev.4.0

DESCRIPTION:

ACJT2 series triacs with high ability to withstand the shock loading of large current provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on inductive load and serious electromagnetic interference place. ACJT2xx-xxF/ACJT2xx-xxFP provides insulation voltage rated at 2000V RMS from all three terminals to external heatsink.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	2	A
V_{DRM}/V_{RRM}	1000	V

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage($T_j=25^\circ\text{C}$)	V_{DRM}	1000	V
Repetitive peak reverse voltage($T_j=25^\circ\text{C}$)	V_{RRM}	1000	V
Non repetitive surge peak Off-state voltage	V_{DSM}	$V_{DRM}+100$	V
Non repetitive peak reverse voltage	V_{RSM}	$V_{RRM}+100$	V
RMS on-state current	$I_{T(RMS)}$	2	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	20	A
I^2t value for fusing (tp=10ms)	I^2t	2	A^2s

Rate of rise of on-state current ($I_G = 2 \times I_{GT}$)	dI/dt	50	A/ μ s
Peak gate current	I_{GM}	1	A
Average gate power dissipation	$P_{G(AV)}$	0.1	W
Peak gate power	P_{GM}	1	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit	
			ACJT210	ACJT225		
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I - II - III	MAX	10	25	mA
V_{GT}		I - II - III	MAX	1.3		V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	I - II - III	MIN	0.2		V
I_L	$I_G=1.2I_{GT}$	I - III	MAX	25	50	mA
		II		35	60	
I_H	$I_T=100\text{mA}$		MAX	10	40	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	600	1000	V/ μ s

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit	
V_{TM}	$I_{TM}=2.8\text{A}$	$t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.55	V
I_{DRM}			$T_j=25^\circ\text{C}$	10	μA
I_{RRM}	$V_D=V_{DRM}$	$V_R=V_{RRM}$	$T_j=125^\circ\text{C}$	1	mA

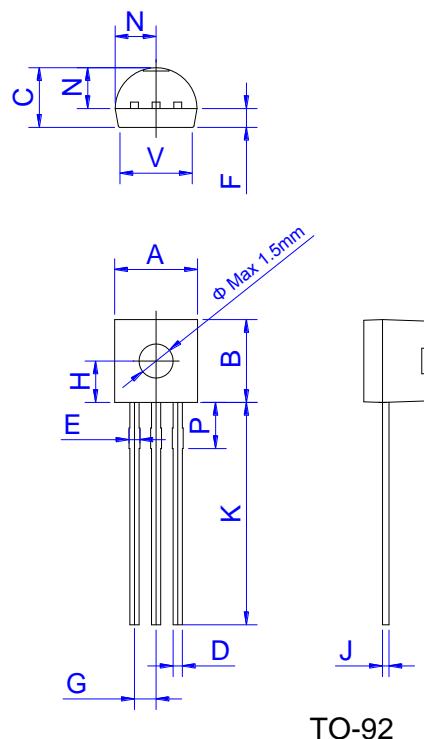
THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-251/ TO-252	4.5
		TO-92	11.2
		SOT-223	5.8
		SOT-89	8.9
		TO-220F(Ins)/ TO-220FP(Ins)	7.5

ORDERING INFORMATION

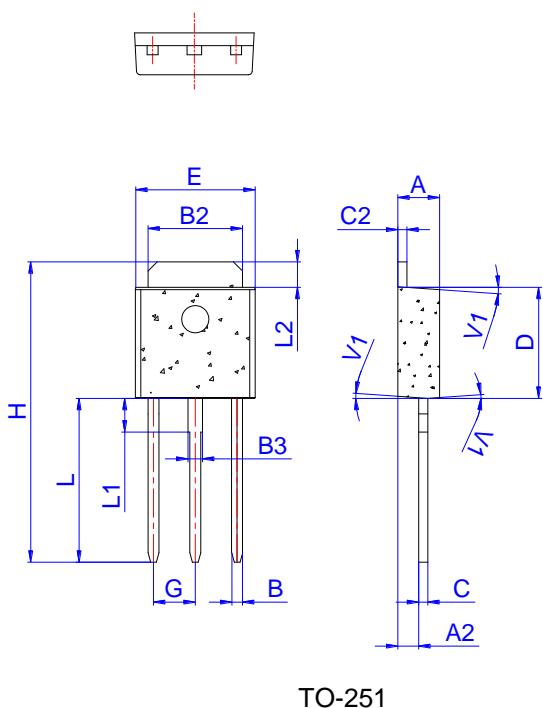
AC	J	T	2	10	-10	U
<u>AC switch</u>						V:SOT-223
<u>JieJie Microelectronics Co.,Ltd</u>						F:TO-220F(Ins)
						FP:TO-220FP(Ins)
			<u>Triacs</u>			U:TO-92 N:SOT-89
				<u>I_{T(RMS)}:2A</u>		H:TO-251 K:TO-252
				10: I _{GT1-3} ≤10mA		
				25: I _{GT1-3} ≤25mA		10: V _{DRM} / V _{RRM} ≥1000V

PACKAGE MECHANICAL DATA

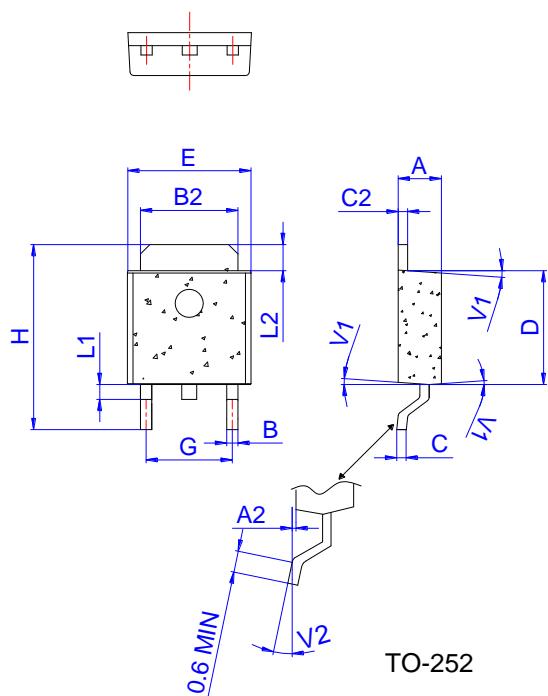


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.60		0.80	0.024		0.031
F	-	1.1	-	-	0.043	-
G	-	1.27	-	-	0.050	-
H	-	2.30	-	-	0.091	-
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
N	2.04		2.66	0.080		0.105
P	1.86		2.06	0.073		0.081
V	-		4.3	-		0.169

PACKAGE MECHANICAL DATA

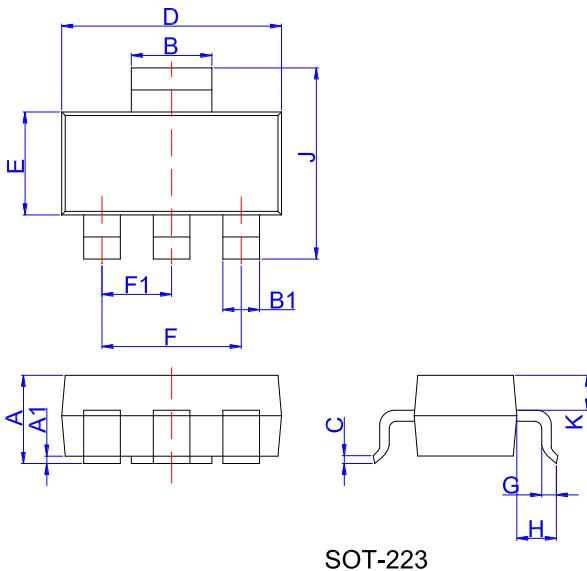


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30				0.091
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°				4°

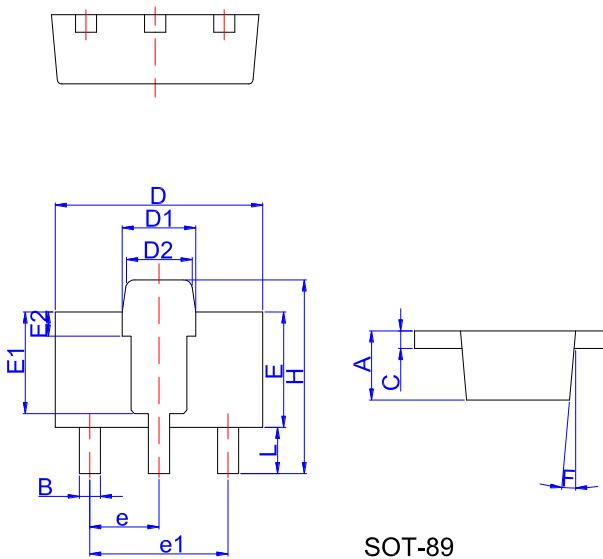


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°				4°
V2	0°		8°	0°		8°

PACKAGE MECHANICAL DATA

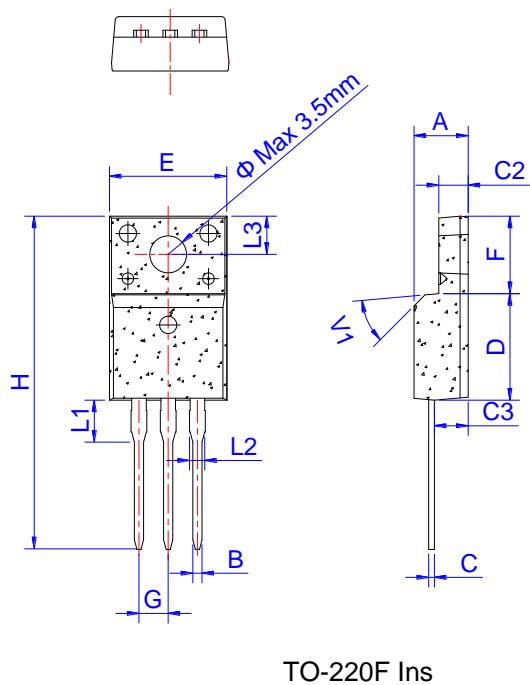


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.5	1.6	1.8	0.059	0.063	0.071
A1	0	0.06	0.10	0	0.002	0.004
B	2.9	3.0	3.1	0.114	0.118	0.122
B1	0.6	0.7	0.8	0.024	0.028	0.031
C	0.22	0.26	0.32	0.009	0.010	0.013
D	6.3	6.5	6.7	0.248	0.256	0.264
E	3.3	3.5	3.7	0.130	0.138	0.146
F		4.6			0.181	
F1		2.3			0.091	
G	0.7	0.9	1.1	0.028	0.035	0.043
H	1.5	1.75	2.0	0.059	0.069	0.079
J	6.7	7.0	7.3	0.264	0.276	0.287
K	0.8	0.9	1.0	0.031	0.035	0.039

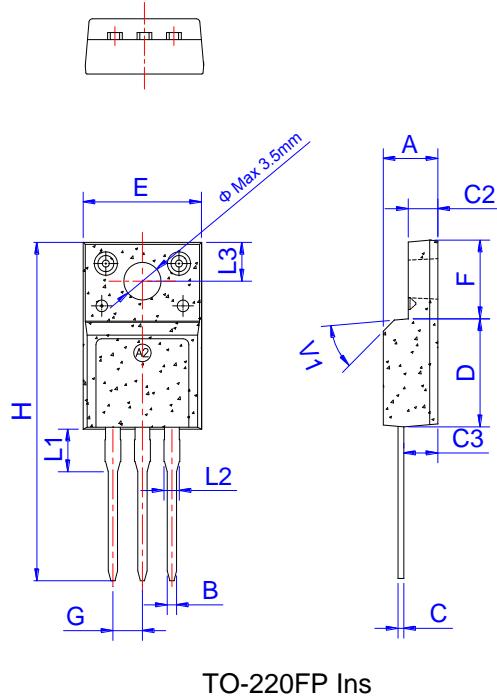


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.40			0.055		0.063
B	0.35			0.014		0.020
C	0.35			0.014		0.018
D	4.30			0.169		0.185
D1	1.50			0.059		0.067
D2	1.30			0.051		0.059
E	2.30			0.091		0.106
E1		2.20			0.087	
E2		0.52			0.020	
e		1.50			0.059	
e1		3.00			0.118	
F		5°			5°	
H	3.94			0.155		0.157
L	0.80			0.031		0.047

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.80	0.173		0.189
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.48		0.75	0.019		0.030
C2	2.40		2.70	0.094		0.106
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.70		10.3	0.382		0.406
F	6.40		7.00	0.252		0.276
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

FIG.1 Maximum power dissipation versus RMS on-state current

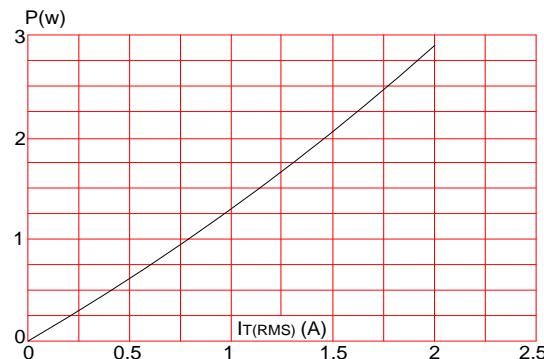


FIG.3: Surge peak on-state current versus number of cycles

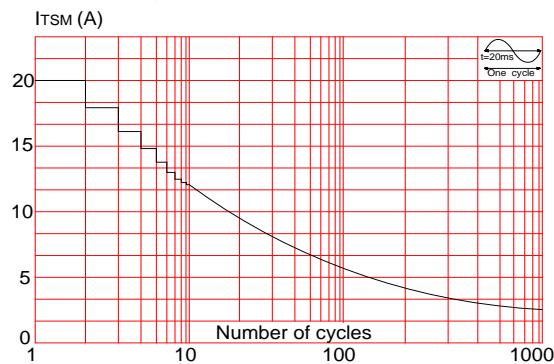


FIG.5: Relative variations of gate trigger current versus junction temperature

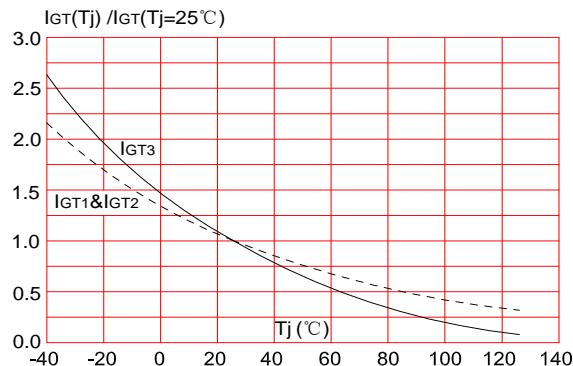


FIG.2: RMS on-state current versus case temperature

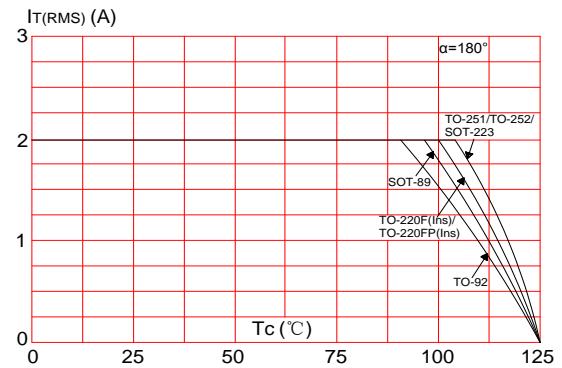


FIG.4: On-state characteristics (maximum values)

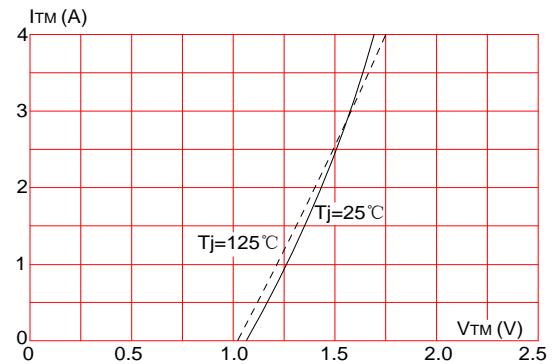
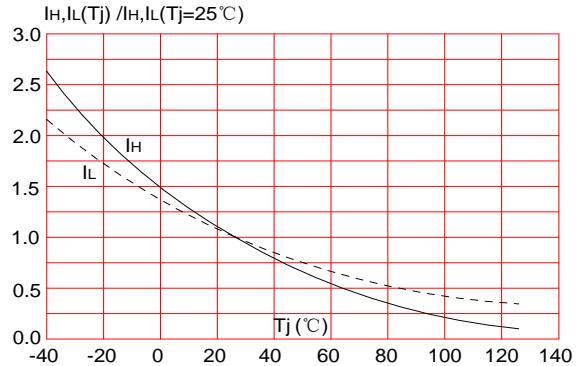


FIG.6: Relative variations of holding current, latching current versus junction temperature



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